



DMT10H032LDV

DUAL 100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	RDS(ON) Max	I _D Max Tc = +25°C			
1001/	36mΩ @ V _{GS} = 10V	18A			
100V	50mΩ @ V _{GS} = 4.5V	16A			

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

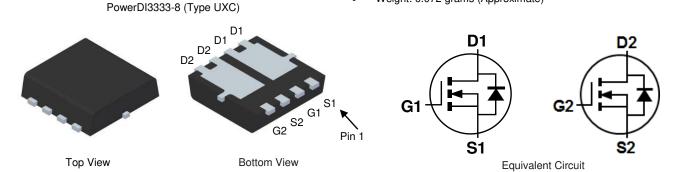
- Power Management Functions
- Analog Switch

Features

- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

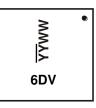
Part Number	Case	Packaging
DMT10H032LDV-7	PowerDI3333-8 (Type UXC)	2,000/Tape & Reel
DMT10H032LDV-13	PowerDI3333-8 (Type UXC)	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \underline{6DV} = Product Type Marking Code\\ \hline \underline{YY}WW = Date Code Marking\\ \hline \underline{YY} = Last Two Digits of Year (ex: 19 for 2019)\\ WW = Week Code (01 to 53) \end{array}$



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 7)	Steady State	Tc = +25°C Tc = +70°C	ID	18 15	А
Maximum Body Diode Forward Current (Note 7)			ls	18	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			ldм	75	A
Pulsed Drain Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			lsм	75	A
Avalanche Current (L = 0.3mH) (Note 8)			las	13	Α
Avalanche Energy (L = 0.3mH) (Note 8)			Eas	25.3	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	130	°C/W
Total Power Dissipation (Note 6)		PD	2.4	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		RθJA	51	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	6.6	-C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						-
Drain-Source Breakdown Voltage	BV _{DSS}	100		_	V	$V_{GS} = 0V, I_D = 1mA$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	_		1	μA	$V_{DS} = 80V, V_{GS} = 0V$
Gate-Source Leakage	lgss			±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	VGS(TH)	1.3	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Descent	—	24	36	mΩ	$V_{GS}=10V,I_D=10A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	34	50	11122	$V_{GS} = 4.5V$, $I_D = 5A$
Diode Forward Voltage	Vsd		0.8	1	V	$V_{GS} = 0V$, $I_S = 6A$
DYNAMIC CHARACTERISTICS (Note 10)						-
Input Capacitance	Ciss	_	683		pF	
Output Capacitance	Coss	_	165		pF	Vps = 50V, Vgs = 0V, f = 1MHz
Reverse Transfer Capacitance	Crss	_	6.9		pF	
Gate Resistance	Rg	—	1.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	6.3	_	nC	
Total Gate Charge (V _{GS} = 10V)	Qg	_	11.9	_	nC	
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{DS} = 50V, I_D = 6A$
Gate-Drain Charge	Qgd	_	3.1		nC	
Turn-On Delay Time	tD(ON)	_	4.1		ns	
Turn-On Rise Time	tR	_	4.5		ns	V _{DS} = 50V, R _L = 5.85Ω
Turn-Off Delay Time	tD(OFF)	_	12.5	_	ns	$V_{GS} = 10V, R_{GEN} = 3\Omega$
Turn-Off Fall Time	tF	_	9.3		ns	1
Reverse Recovery Time	trr	_	31.5		ns	
Reverse Recovery Charge	QRR	_	94.6	—	nC	I⊧ = 6A, di/dt = 500A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Bevice mounted on FR-4 substrate PC board, 202 copper, with 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).

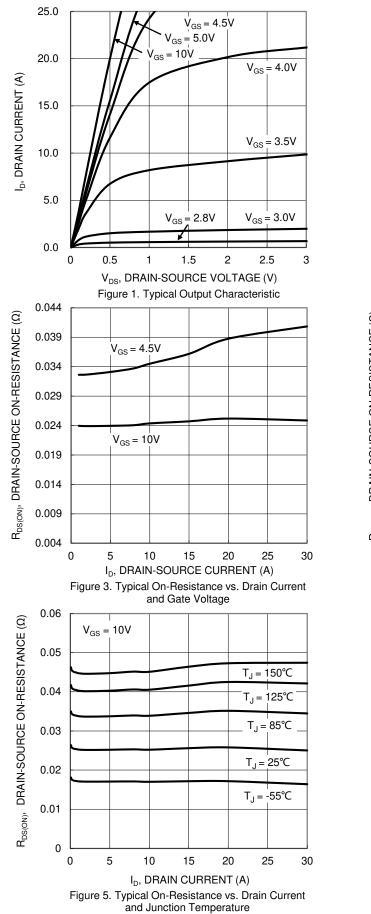
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

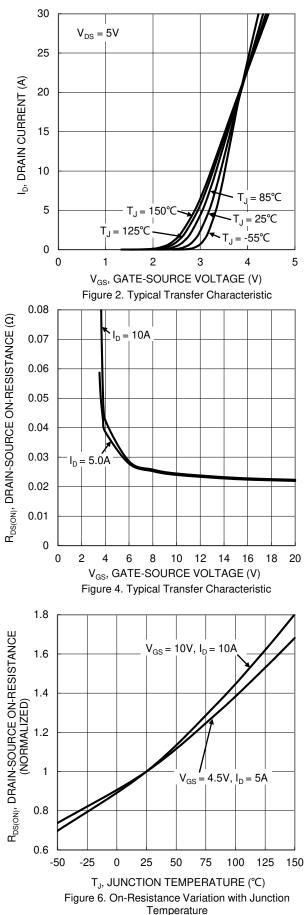
9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.



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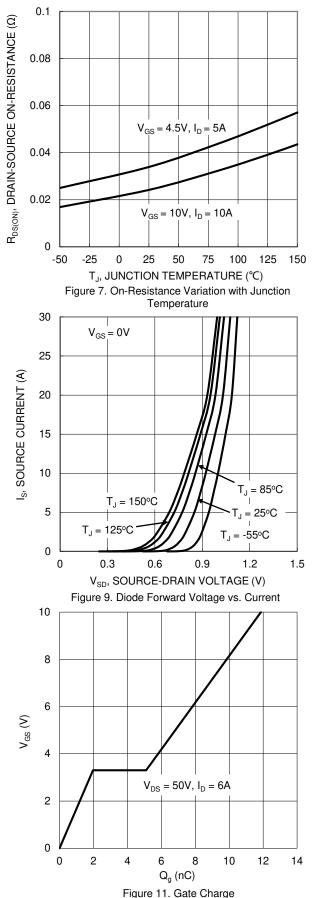


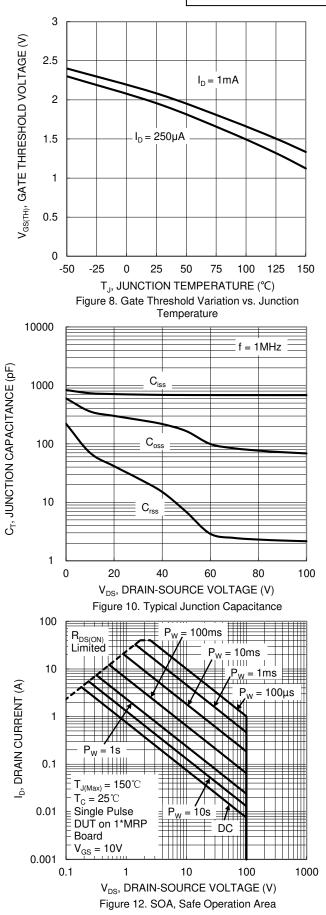


DMT10H032LDV Document number: DS42043 Rev. 3 - 2

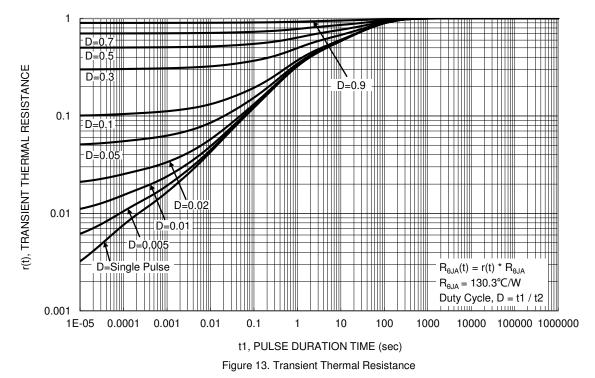


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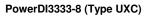


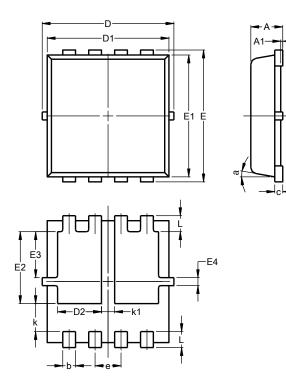




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



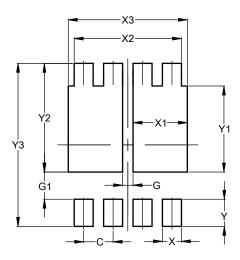


PowerDI3333-8 (Type UXC)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	0.90	1.30	1.10		
E	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	-	0.65		
L	0.30	0.50	0.40		
k	0.50	0.90	0.70		
k1	0.13	0.53	0.33		
а	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)		
С	0.650		
G	0.230		
G1	0.600		
Х	0.420		
X1	1.200		
X2	2.370		
X3	2.630		
Y	0.600		
Y1	1.900		
Y2	2.400		
Y3	3.600		



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